

Title (en)

METHOD AND APPARATUS FOR CONDUCTING HEAT TO OR FROM AN ARTICLE BEING TREATED UNDER VACUUM

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Application

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Priority

US 7540179 A 19790914

Abstract (en)

[origin: US4261762A] A method and apparatus are disclosed for providing heat conduction between an article being treated in a vacuum and a support member by providing a gas under pressure of about 0.5 to 2.0 Torr between the article and the support member. The method and apparatus are described for use in a semiconductor wafer ion implantation system wherein the wafer is clamped to the support member which is cooled. A seal can be provided between the wafer and the support member adjacent the periphery of the article.

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FR2520929A1; FR2505881A1; FR2516308A1; US5370739A; US5356476A; US5647911A; US5908508A; DE3047441A1; DE3051188C2; EP0046154B1

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